

Amendment of the Claims

The following list of claims replaces all previous version(s) of claims.

1. (Previously Presented) A trench-type storage device comprising:
a substrate;
at least one trench in said substrate;
conductive carbon nanotubes lining said trench; and
a trench conductor filling said trench,
wherein said trench conductor and said substrate having a co-planar top surface.
2. (Previously Presented) A trench-type storage device comprising:
a substrate;
at least one trench in said substrate;
conductive carbon nanotubes lining said trench;
a trench conductor filling said trench; and
a trench dielectric between said carbon nanotubes and sidewalls of said trench.
3. (Previously Presented) The storage device in claim 1, further comprising a layer of trench dielectric on top of a bottom of said trench and between said carbon nanotubes and sidewalls of said trench, wherein the conductive carbon nanotubes form an open cylinder structure lining said sidewalls of said trench through said layer of trench dielectric.
4. (Previously Presented) The storage device in claim 1, wherein the trench conductor comprises at least one of polysilicon, a metal, and an alloy thereof, contacting said layer of trench dielectric on top of said bottom of said trench.
5. (Previously Presented) The storage device in claim 1, characterized in that the conductive carbon nanotubes and the trench conductor are disposed in the trench, and the trench conductor is carbon free.

6. (Original) The storage device in claim 1, characterized in that the substrate is free of carbon nanotube catalyst materials.
7. (Original) The storage device in claim 1, characterized in that the carbon nanotubes form a consistent lining along approximately the entire length of sidewalls of said trench.
8. (Previously Presented) The storage device in claim 2, characterized in that the trench-type storage device is planarized so that a top surface of the substrate is coplanar with respective top surfaces of the trench dielectric, the conductive carbon nanotubes and the trench conductor.
9. (Original) The storage device in claim 1, characterized in that the conductive carbon nanotubes are grown downwards into the trench.
10. (Previously Presented) The storage device in claim 1, further comprising a trench dielectric between said carbon nanotubes and sidewalls of said trench.
11. (New) A trench-type storage device comprising:
 - a substrate;
 - at least one trench in said substrate;
 - conductive carbon nanotubes forming an open cylinder in lining said trench; and
 - a trench conductor filling said open cylinder of said carbon nanotubes,wherein said trench conductor and said substrate having a co-planar top surface.
12. (New) The storage device in claim 11, wherein the trench conductor comprises at least one of polysilicon, a metal, and an alloy thereof, contacting said layer of trench dielectric on top of said bottom of said trench.

13. (New) The storage device in claim 11, characterized in that the conductive carbon nanotubes and the trench conductor are disposed in the trench, and the trench conductor is carbon free.

14. (New) The storage device in claim 11, characterized in that the substrate is free of carbon nanotube catalyst materials.

15. (New) The storage device in claim 11, characterized in that the carbon nanotubes form a consistent lining along approximately the entire length of sidewalls of said trench.

16. (New) The storage device in claim 11, characterized in that the conductive carbon nanotubes are grown downwards into the trench.

17. (New) The storage device in claim 11, further comprising a trench dielectric between said carbon nanotubes and sidewalls of said trench.